

Abstract Submitted  
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**Lattice thermal conductivity of nanostructured semiconductors from atomistic simulations**<sup>1</sup> YUPING HE, DAVIDE DONADIO, University of California Davis, JOO-HYOUNG LEE, JEFFREY C. GROSSMAN, University of California Berkeley, GIULIA GALLI, University of California Davis — We present an atomistic analysis of the thermal conductivity ( $k$ ) of nanoporous silicon (np-Si) [1, 2], and we compare our results with those obtained for bulk crystalline (c-Si) and amorphous Si. We computed  $k$  using equilibrium molecular dynamics and Green Kubo relations; we then analyzed our results by solving the Boltzmann Transport Equation in the single mode relaxation time approximation, and by using an approach devised [3] to describe thermal transport in disordered semiconductors. We observe that in np-Si the phonon mean free path is reduced by up to a factor of 10 with respect to c-Si, yielding a reduction of the  $k$  of about 2 orders of magnitude. The predominant phonon scattering processes contributing to  $k$  can be modeled by the same non-perturbative [3] approach that describes thermal transport in a-Si.

[1] J-H. Lee, et al. Appl. Phys. Lett, 91, 223110 (2007)

[2] J-H. Lee, et al., Nano. Lett., 8(11), 3750 (2008)

[3] P. B. Allen and J. L. Feldman, Phys. Rev. B 48, 12581 (1993)

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Yuping He  
University of California Davis

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